

Could We Make SSDs Self-Healing?

Tong Zhang

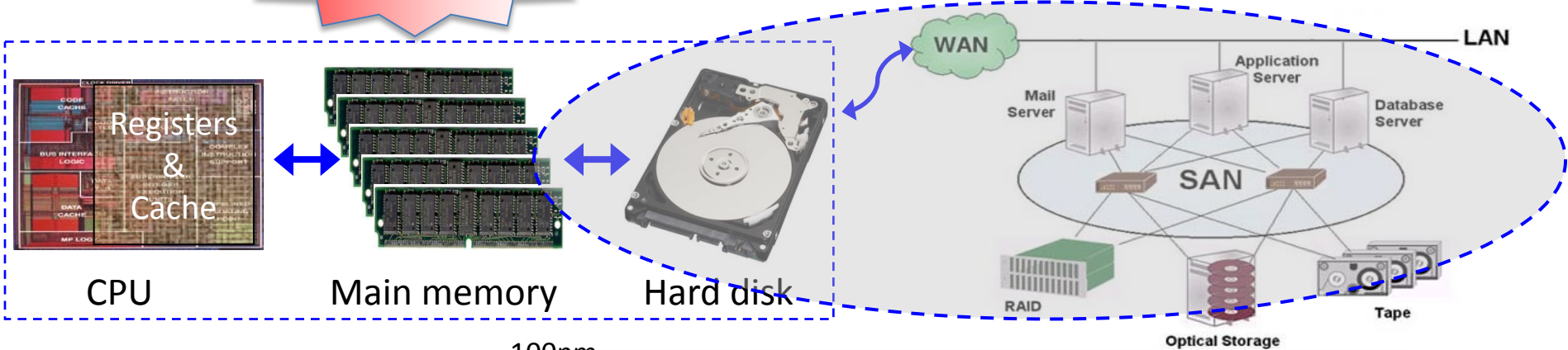
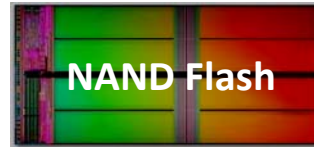
Electrical, Computer and Systems Engineering Department

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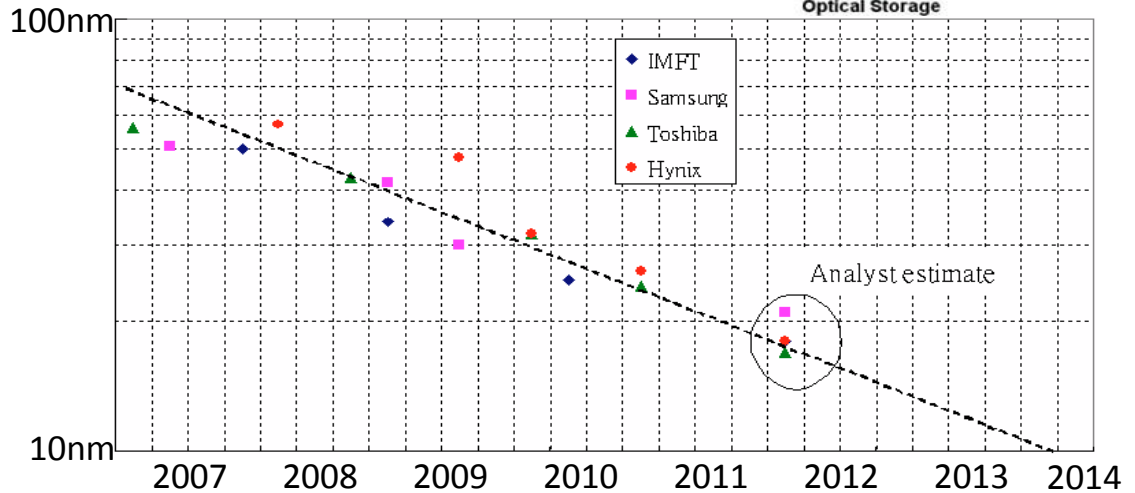
Google/Bing: "tong rpi"

Introduction and Motivation

Hot Topic



Bit cost reduction

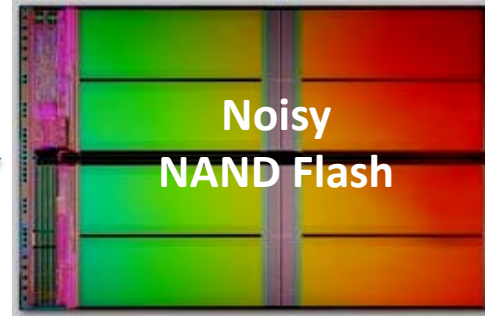


Introduction and Motivation

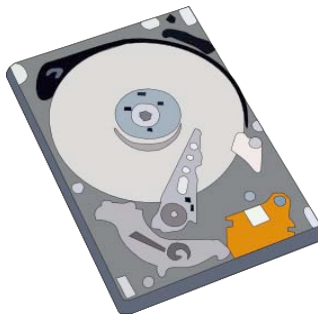
Error Rate Endurance Retention



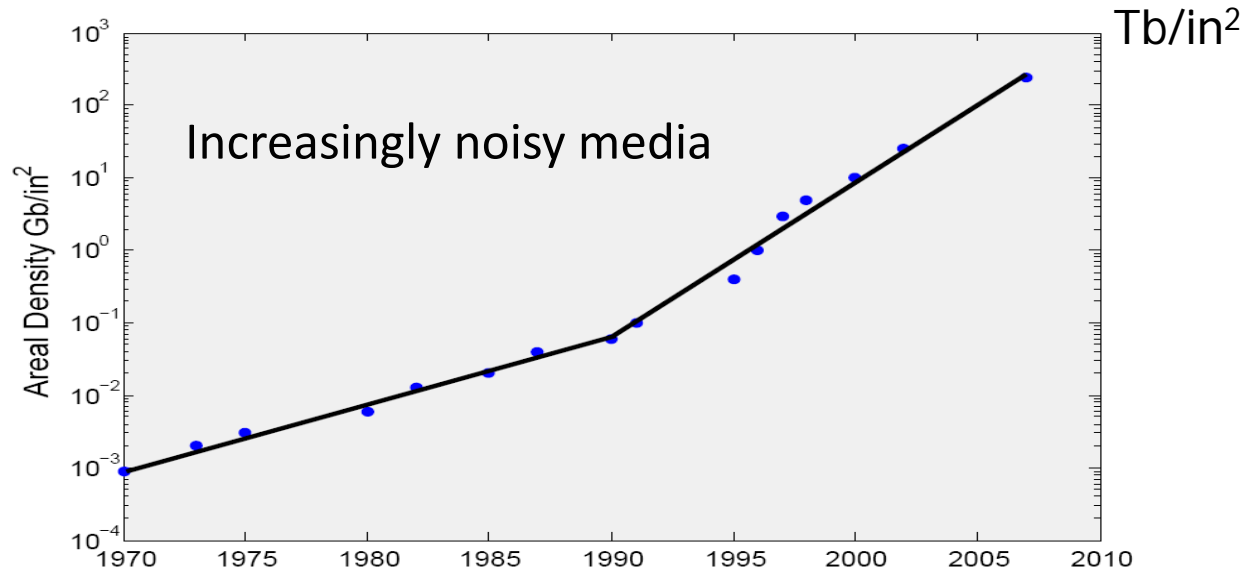
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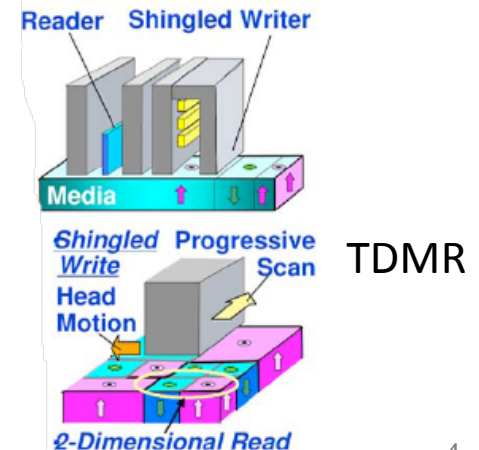
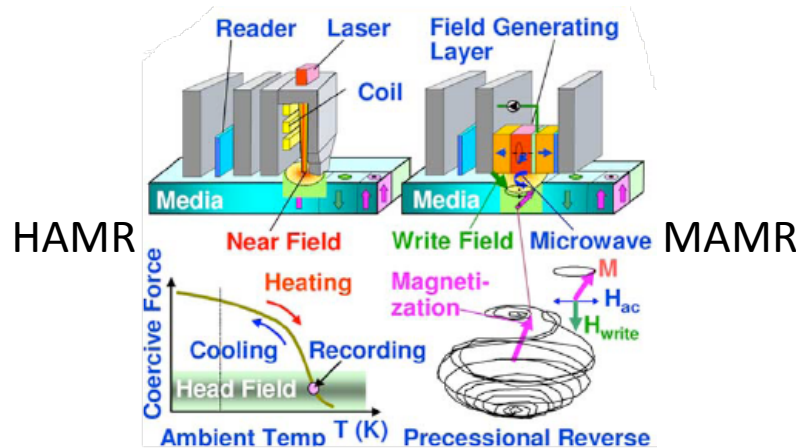
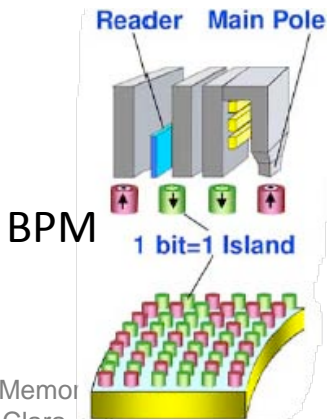
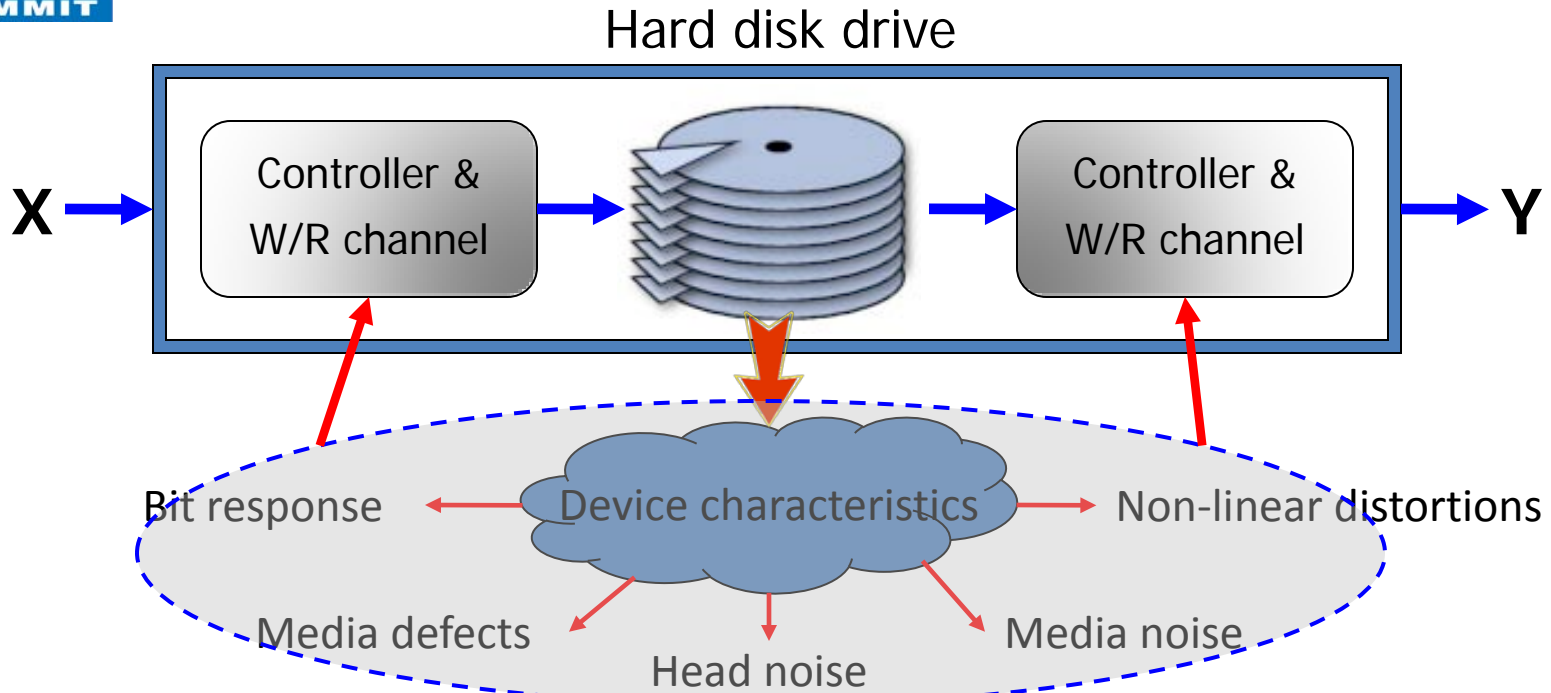
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Hard disk drive

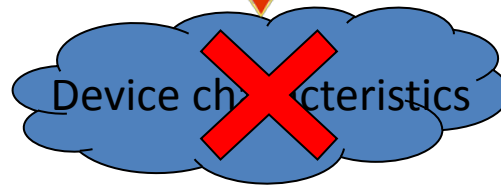
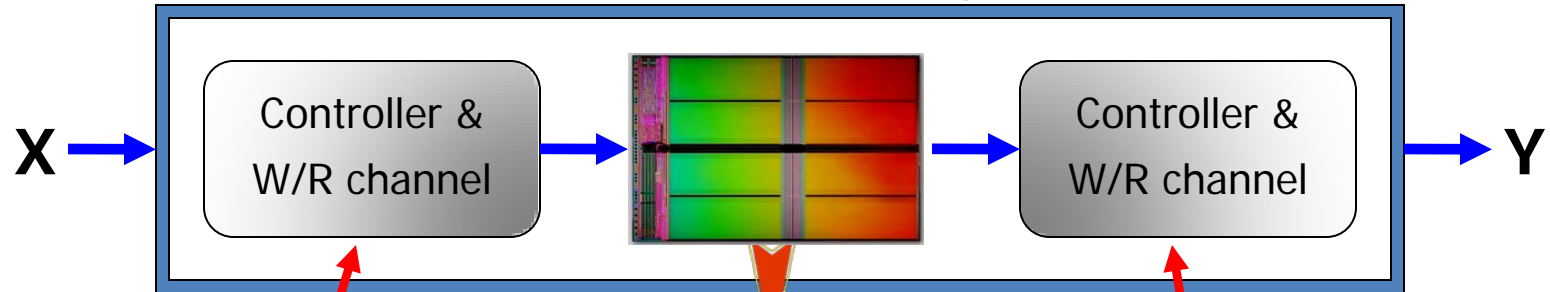


In-Depth Knowledge of Storage Media



In-Depth Knowledge of Storage Media

Solid-State Storage



Write latency	Read latency	Erase latency	Endurance	Redundancy	...



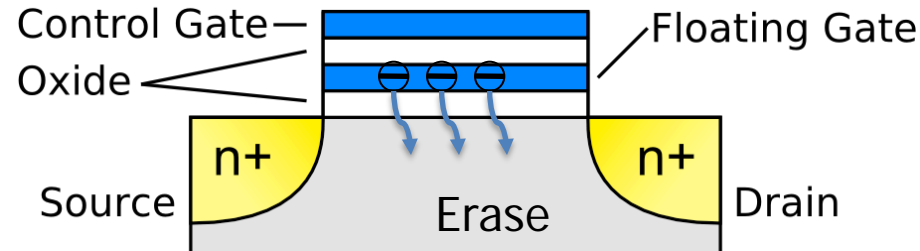
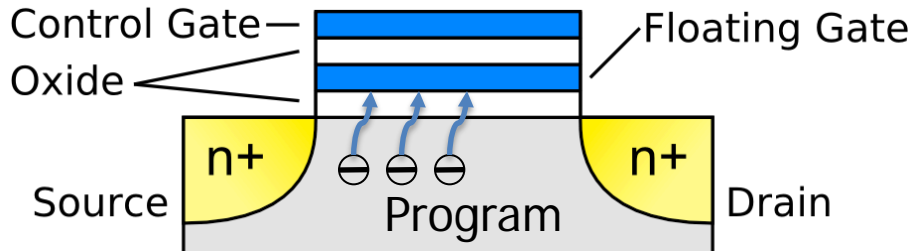
Painless system designers' life



Lost system optimization opportunities

Device-Aware SSD System Design

Device Wear-Out



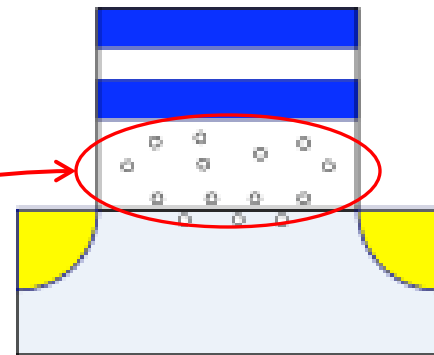
Modulate transistor threshold voltage



Program/erase (P/E) cycling

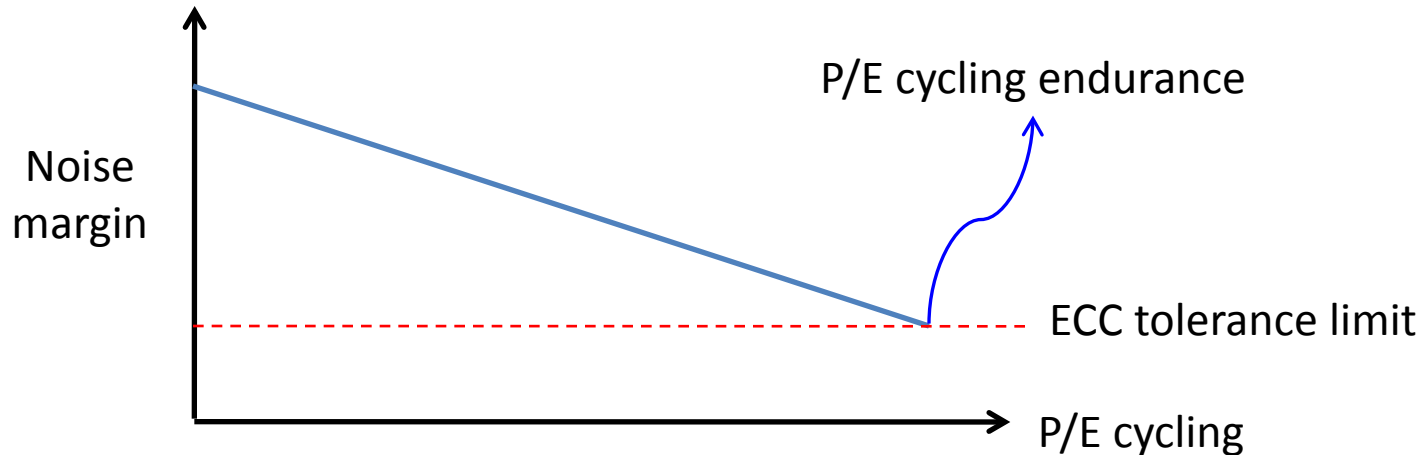
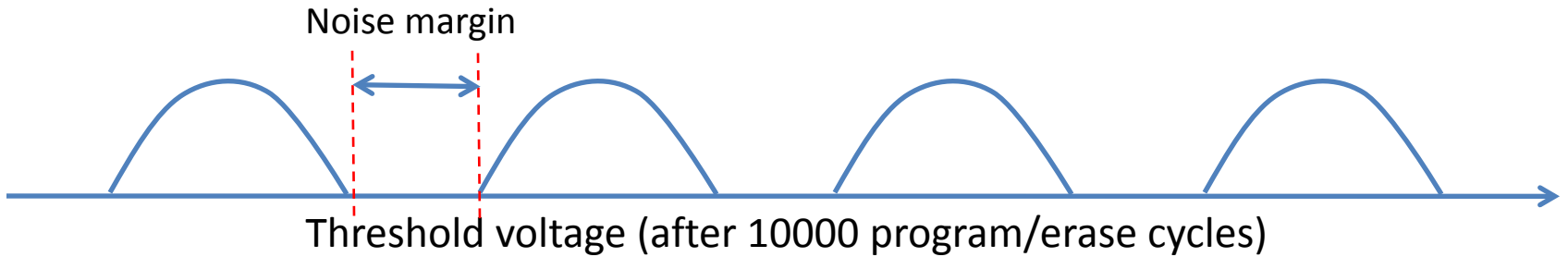
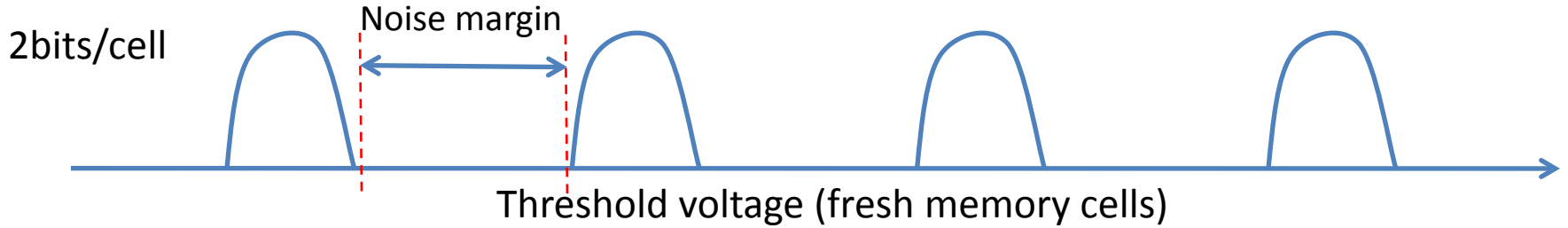
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Accumulates charge traps

1. Larger random telegraph noise
2. Larger threshold voltage degradation during retention
3. Larger program/read disturb

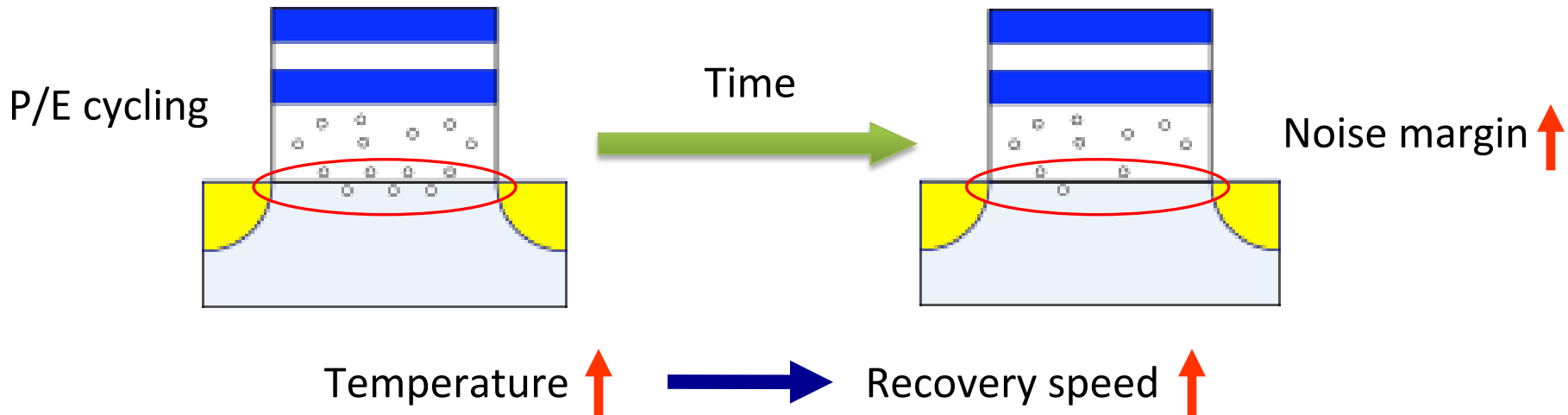
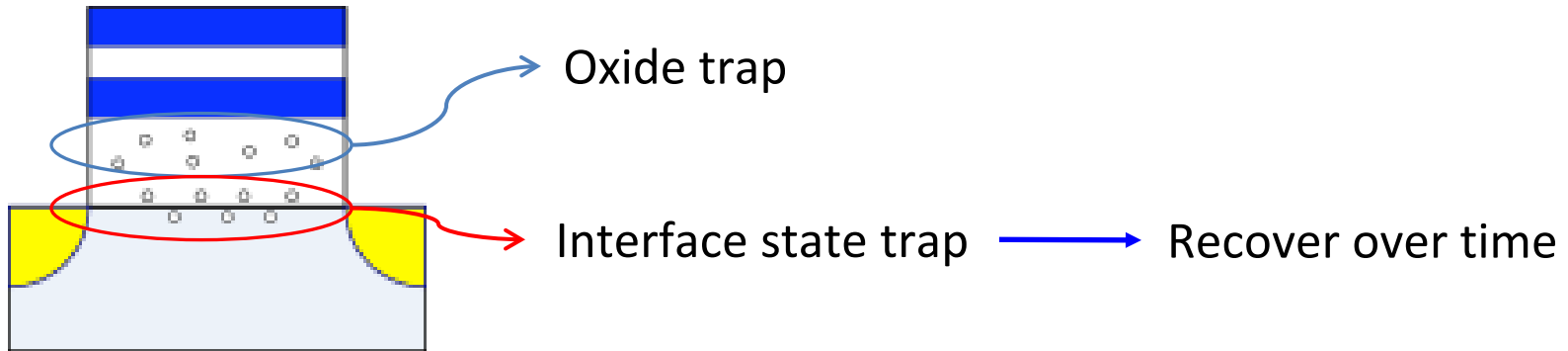


Smaller noise margin

Device Wear-Out

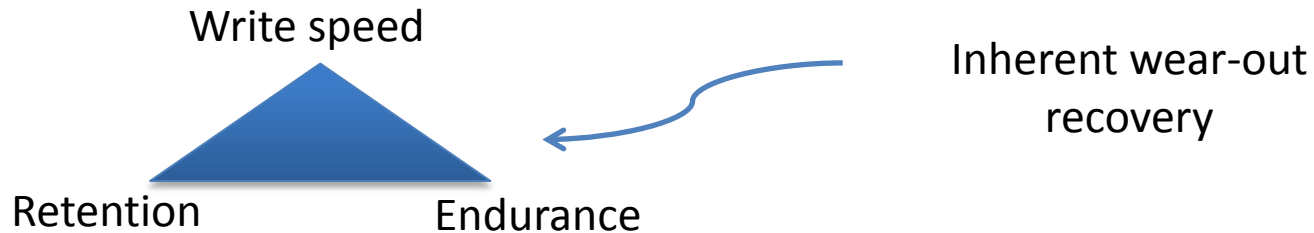


Device Wear-Out Recovery



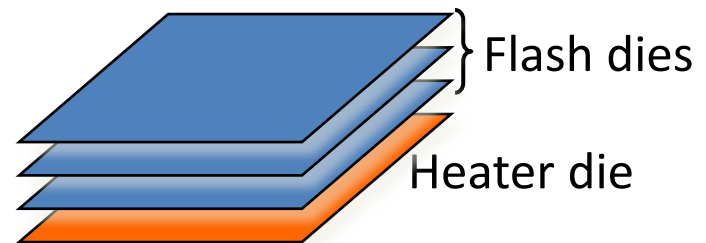
Self-Healing SSD?

- ❑ Explicitly leverage this device wear-out recovery phenomenon in FTL
 - Re-think of how to utilize existing over-provisioning?
 - Keep track of the history of environment temperature
- ❑ Intentionally operate SSDs under higher environment temperature

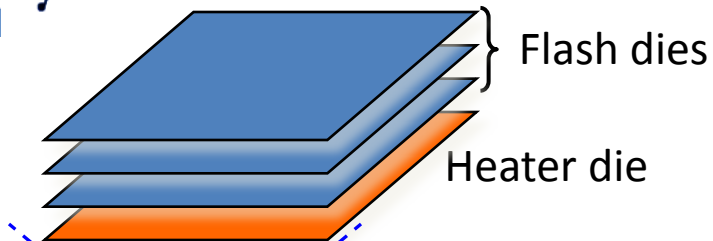


Most Aggressive Scenario

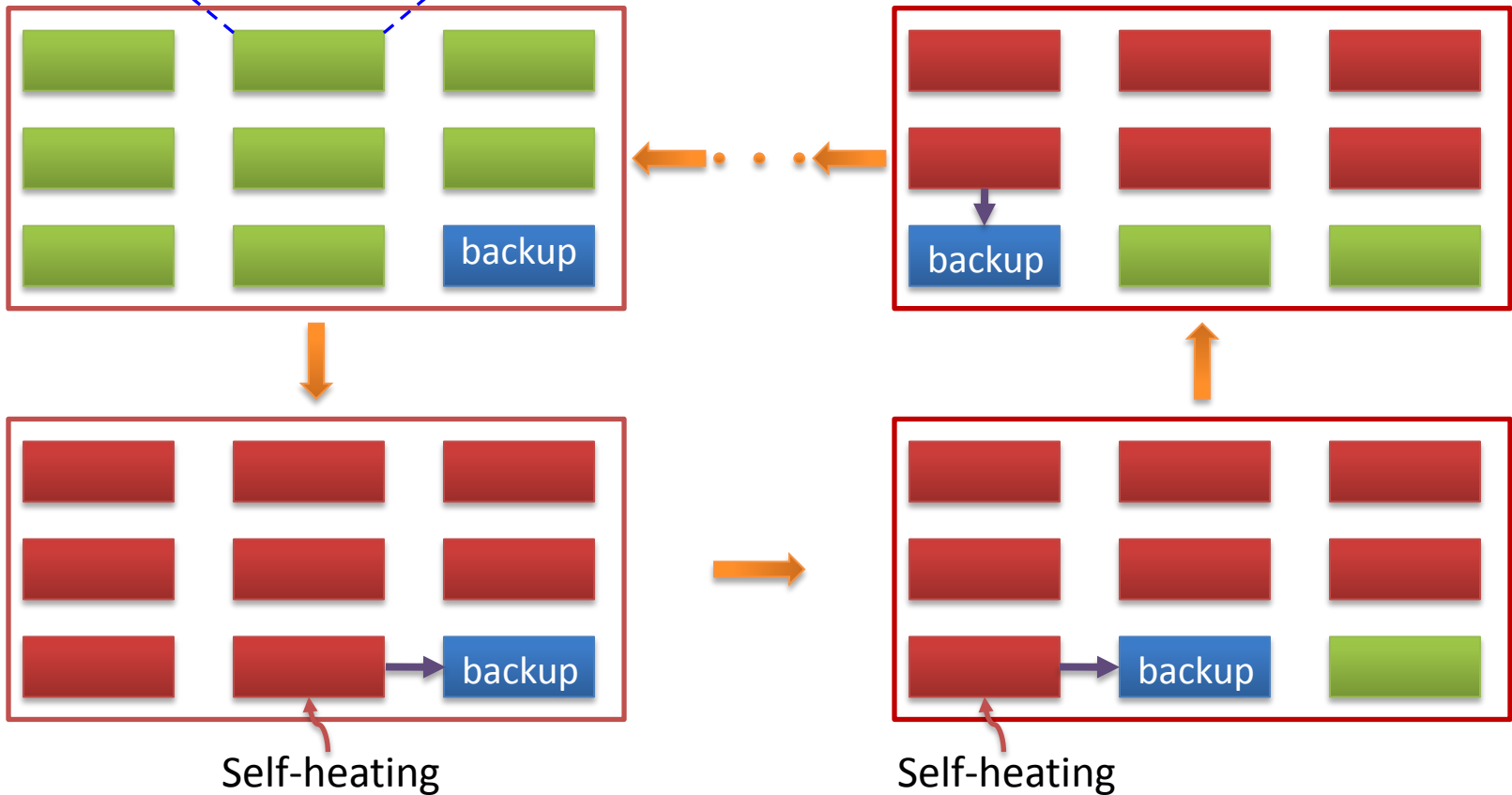
➤ 3D-enabled self-heating flash chip



Self-Healing SSD?



- ✓ Improve P/E cycling endurance
- ✓ Improve write speed
- ✓ Increase retention time



A Preliminary Evaluation

 Improve P/E cycling endurance

Thermal modeling

- Heating time
- Heating energy

Flash cell modeling

- Cell-to-cell interference
- Random telegraph noise
- Retention noise

Self-healing
SSD simulation

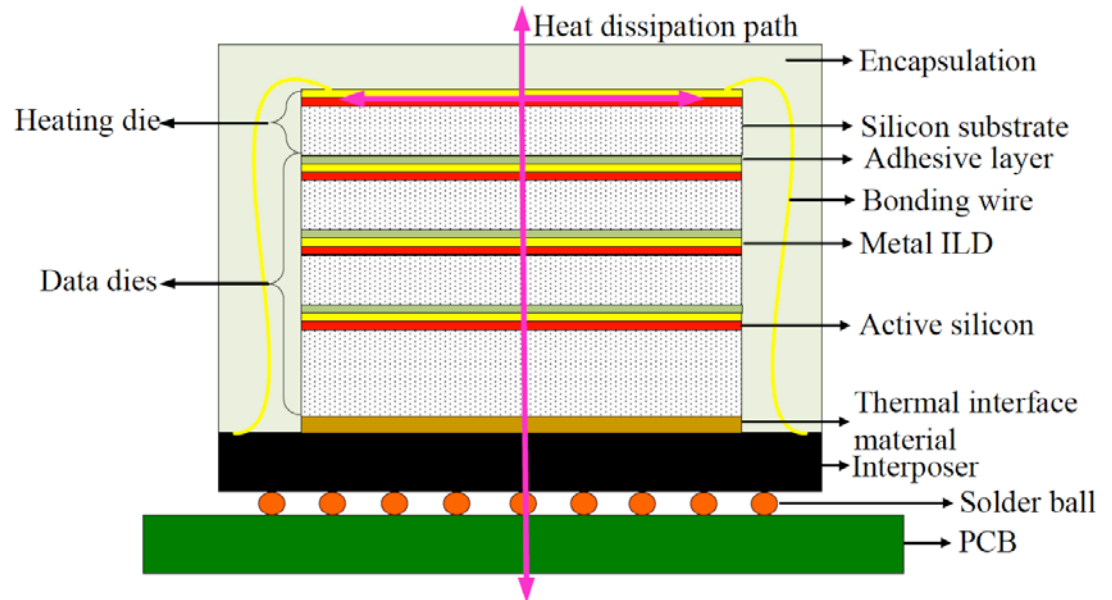
SSD system modeling

- Impact of data backup on system performance

Thermal Simulation Setup

HotSpot thermal modeling

3D chip structure

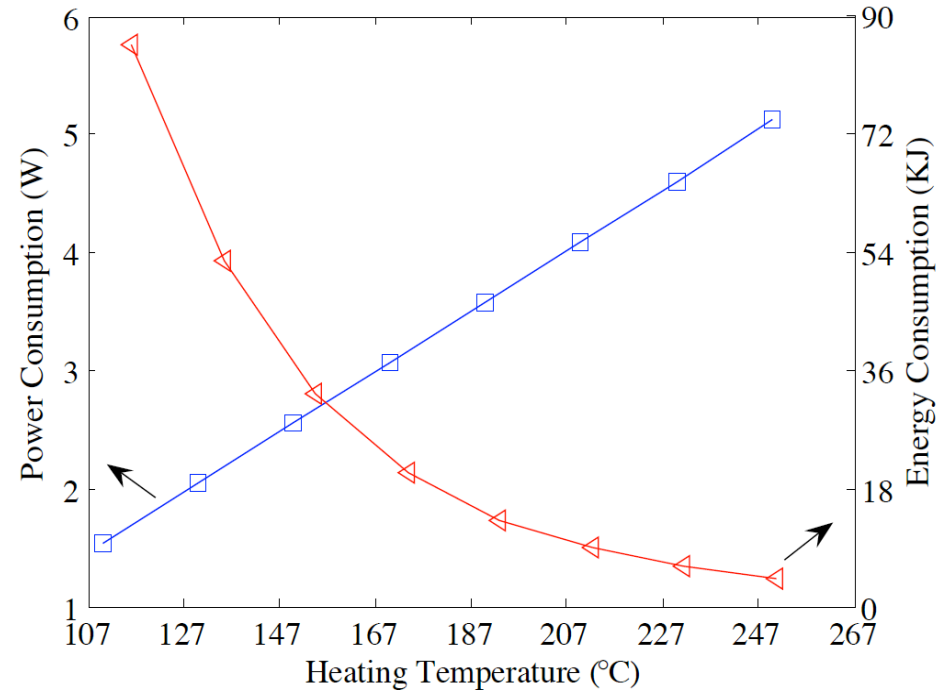
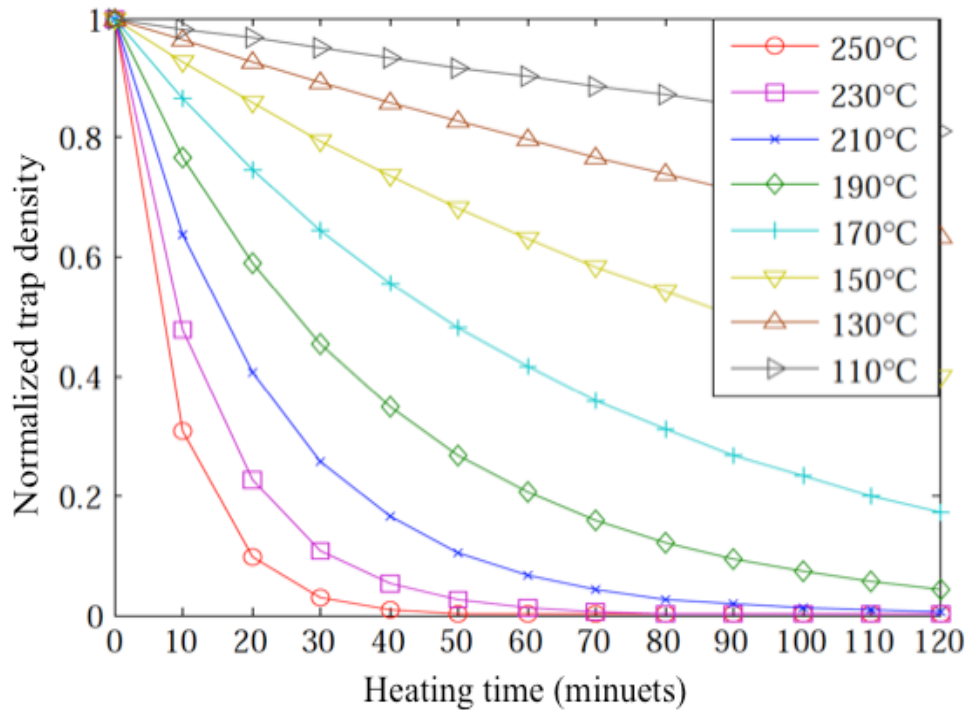


3D chip setup



Layer	Thermal conductivity	Thickness
Encapsulation	0.453 W/(mk)	1.0 mm
Silicon substrate	100 W/(mK)	50 μ m
Adhesive material	4 W/(mk)	4 μ m
Metal ILD	200 W/(mk)	8 μ m
Active silicon	100 W/(mk)	2 μ m
Thermal interface material	4 W/(mk)	20 μ m
Interposer	2 W/(mk)	0.4 mm
Solder balls	16.7 W/(mk)	0.94 mm
PCB	3 W/(mk)	2 mm

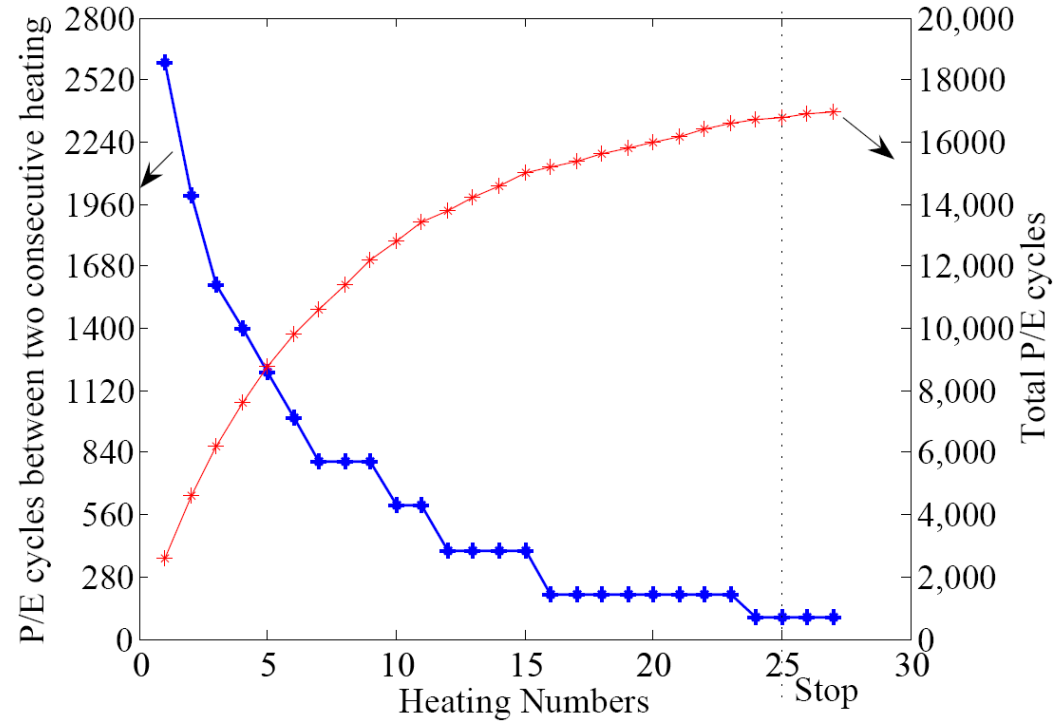
Thermal Simulation Results



- ❑ 1.5W to 5.1W power consumption when temperature changes from 110 to 250C
- ❑ Choose 200°C as the target heating temperature
- ❑ ~35 minutes for 80% interface state traps to recover

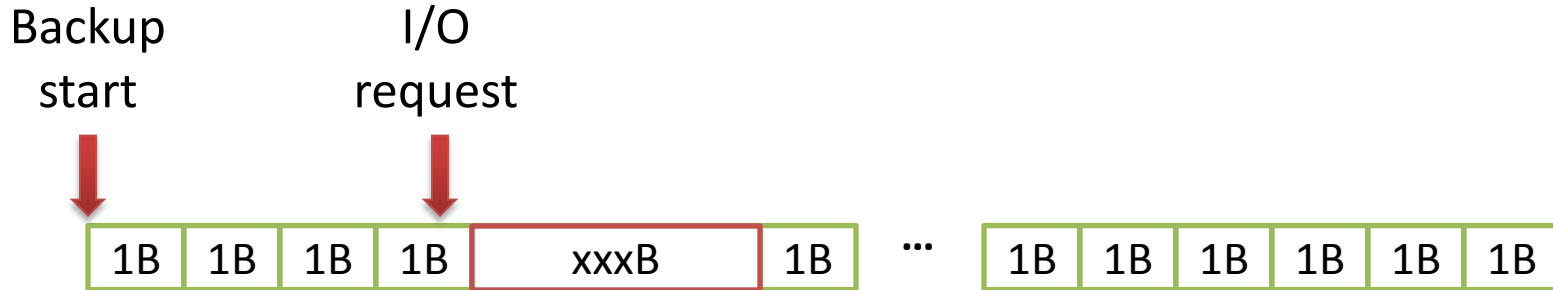
P/E Cycling Endurance Improvement

- Allowable worst-case memory read raw BER of $2.04e-3$
- 10-year retention limit
- Include trap recovery under normal temperature (45°C)
- Self-healing trigger BER $1.50e-3$
- Three times longer cooling time



P/E cycling endurance: 3000 → 17400

Data Backup During Chip Self-Heating



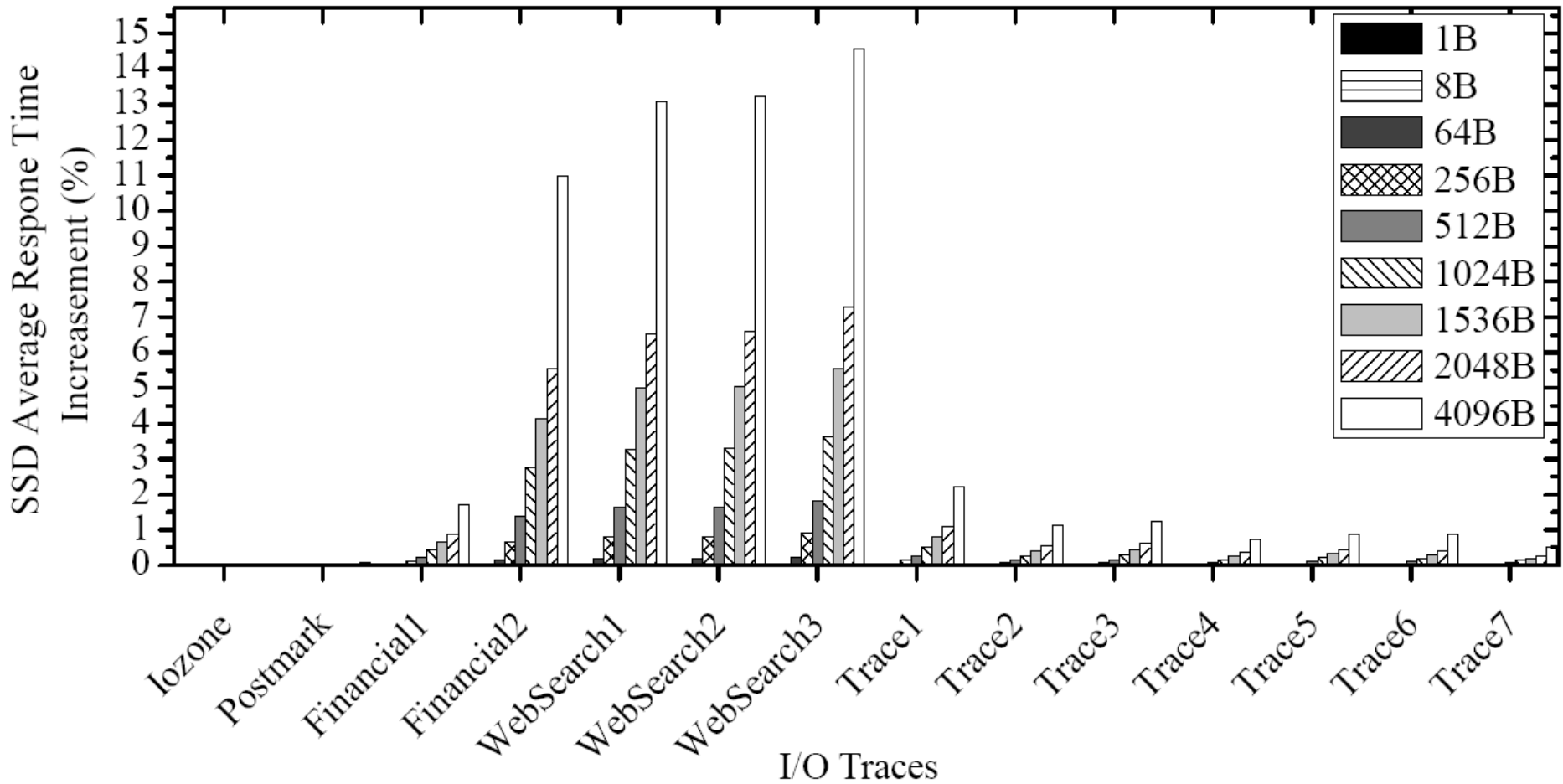
- Initialize data backup when SSD is idle
- I/O request can interrupt data backup operation
- Impact of data backup granularity on I/O request response time
- Need to handle read and write conflict



Simulation Setup

- DiskSim simulator with SSD model patch
- 2 dies/chip, 8-bit I/O bus and a number of common control bus
- 2 planes/die, 2048 blocks/plane, 64 pages/block, 8 sectors/page, 512bytes/sector
- 2 channels, 17 flash chips/channel including one backup chip
- Backup chip on each channel only backups the data of the flash chips on the same channel
- ONFI 2.0, 133MB/s, read access time $50\mu\text{s}$, program time $600\mu\text{s}$

Simulation Setup



Summary

- ❑ Continuous technology scaling demands true device-aware SSD system design
- ❑ How to exploit memory cell wear-out recovery?
 - Explicitly leverage this wear-out recovery phenomenon in FTL
 - A more aggressive scenario: self-heating NAND flash memory chips
 - SSD controller scheduling and data backup strategy
 - Simulation based on detailed thermal, flash memory cell, and SSD system modeling
- ❑ Comprehensive cross-layer optimization: **an open question**